

TECHNICAL DATA DATA SHEET 5086, REV. A.3

AVAILABLE AS 1N, JAN, JANTXV JANS

# **V<sub>F</sub> Controlled Diodes**

Qualified per MIL-PRF-19500/241

#### **DESCRIPTION:**

This voidless hermetically sealed Vf controlled diode is military qualified per MIL-PRF-19500/241 and is targeted for space, commercial and military aircraft, military vehicles, shipboard markets and all high reliability applications.

### **FEATURES / BENEFITS:**

- ✓ Hermetic, non-cavity glass package
- ✓ Category I Metallurgically bonded
- ✓ All devices are 100% hot solder dipped
- ✓ JAN/ JANTX/ JANTXV available per MIL-PRF-19500/241

### **MAXIMUM RATINGS:**

- ✓ Operating and Storage Temperature: -65°C to +175°C
- ✓ Forward Voltage (max): 1Vdc @ 200mA, .92Vdc @ 100mA
- ✓ Reverse Leakage Current (max): 1 nAdc @ V<sub>R</sub>

#### **ELECTRICAL CHARACTERISTICS:**

All ratings are at  $T_A = 25^{\circ}$ C unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Working Peak Reverse Voltage (V <sub>RWM</sub> )		125	-	-	V (pk)
Average Rectified Output Current (I <sub>o</sub> )	$T_A = 75^{\circ}C$	-	-	150	mA dc
Surge Peak Forward Current (I <sub>FSM</sub> ) @ T <sub>A</sub> =25°C	t <sub>p</sub> = 1s	-	-	500	mA (pk)
Thermal Resistance (R <sub>0,JL</sub> )	L=.375 in	-	-	250	°C/W
Thermal Resistance (R <sub>0JC</sub> )	L=0	-	-	40	°C/W
Thermal Resistance (R <sub>0JX</sub> )				245	°C/W
Junction Temperature (T <sub>J</sub> )	-	-65	-	+175	°C
Storage Temp. (T <sub>stg</sub> )	-	-65	-	+175	°C



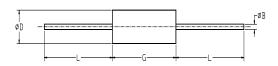
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CHARACTERISTIC		CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage		$\begin{array}{c} V_{F1} \text{ at } I_{F1} = 200 \text{ mA dc} \\ V_{F2} \text{ at } I_{F2} = 100 \text{ mA dc} \\ V_{F3} \text{ at } I_{F3} = 50 \text{ mA dc} \\ V_{F4} \text{ at } I_{F4} = 10 \text{ mA dc} \\ V_{F5} \text{ at } I_{F5} = 5 \text{ mA dc} \\ V_{F6} \text{ at } I_{F6} = 1 \text{ mA dc} \\ \end{array}$	0.83 0.79 0.74 0.65 0.60 0.52	-	1.0 0.92 0.88 0.80 0.765 0.70	V
Maximum Reverse Leakage Current		I <sub>RM1</sub> @ V <sub>RWM</sub> I <sub>RM2</sub> @ V <sub>RWM</sub> . T <sub>A</sub> = 150 °C	-	-	1 3	nA dc μA
Breakdown Voltage	(BV <sub>R</sub> )	I <sub>R</sub> = 100μA, T <sub>A</sub> = -55 °C	150	-	-	V
Junction Capacitance	(C <sub>J</sub> )	$V_R = 0Vdc, f = 1MHz$	-	-	8.0	pF

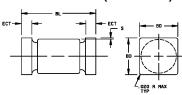
<sup>\*</sup>Sensitron **space equivalent diodes** are manufactured and screened to MIL-PRF-19500 flow and guidelines starting from wafer fabrication through assembly and testing using our internal specification.

### **PACKAGE DIMENSIONS (inches/mm)**





## MELF (Add "US")



1N3595-1

PACKAGE	DIMENSIONS - INCHES (MILLIMETERS)			
STYLE	φВ	φD	G	L
	.018/.022	.056/.075	.140/.180	1.00/1.5
DO-35	0.46/0.56	1.42/1.91	3.56/4.57	25.4/38.10

### 1N3595US

PACKAGE	DIMENSIONS - INCHES (MILLIMETERS)			
STYLE	BL	BD	S	ECT
	.165/.195	.070/.085	0.003	.019/.028
D-5D	4.19/4.95	1.78/2.16	Min	0.48/0.71

### **PART ORDERING INFORMATION:**

The following part numbers can be purchased in either axial or surface mount devices and screened and tested to the military screening flow. The parts are marked in accordance with the testing performed, example:

Sensitron Screening Level	*Part Number Leaded Package (example for 1N3595-1)	*Part Number Surface Mount Package (example for 1N3595US)
1N	1N3595-1	1N3595US
JAN	JAN1N3595-1	JAN1N3595US
JANTX	JANTX1N3595-1	JANTX1N3595US
JANTXV	JANTXV1N3595-1	JANTXV1N3595US
JANS	JANS1N3595-1	JANS1N3595US

<sup>\*</sup>Parts can also be ordered Tape & Reel



1N3595-1, 1N3595US VF CONTROLLED DIODE

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